

[ABSTRACT]

Described herein is a technique capable of exhausting a process gas in a wide pressure range. According to one aspect of the technique, there is provided a substrate
5 processing apparatus including: a process chamber; a gas supply system configured to supply a process gas containing a compound capable of reacting with a metal; and a gas exhaust system configured to exhaust an inner atmosphere of the process chamber, wherein the gas exhaust system includes: a common exhaust piping; a first exhaust piping made of a resin incapable of reacting with the compound and whose one end is
10 connected to the common exhaust piping via a first valve and the other end is connected to a first exhauster; and a second exhaust piping made of the metal and whose one end is connected to the common exhaust piping via a second valve and the other end is connected to a second exhauster.